Silicon NPN transistor in a TO-92 Plastic Package.

High voltage, low saturation, low $C_{cb.}$

High voltage control circuit.

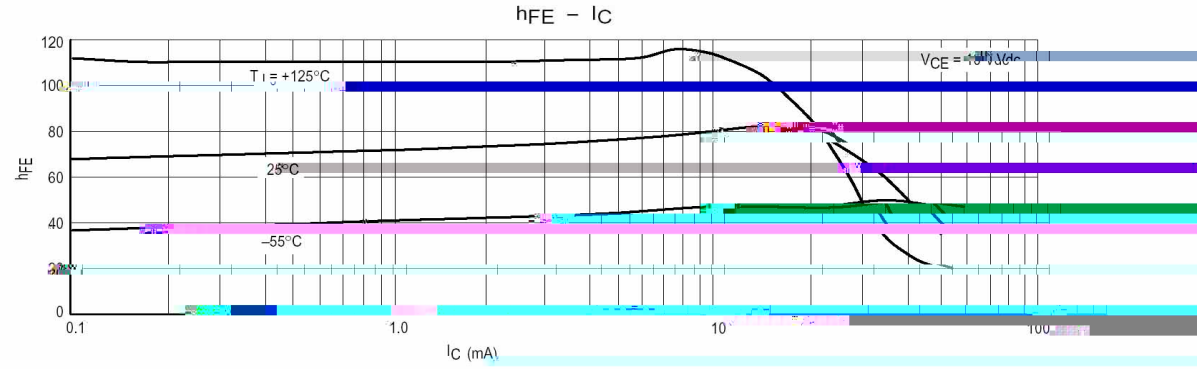
/ Absolute Maximum Ratings(Ta=25)

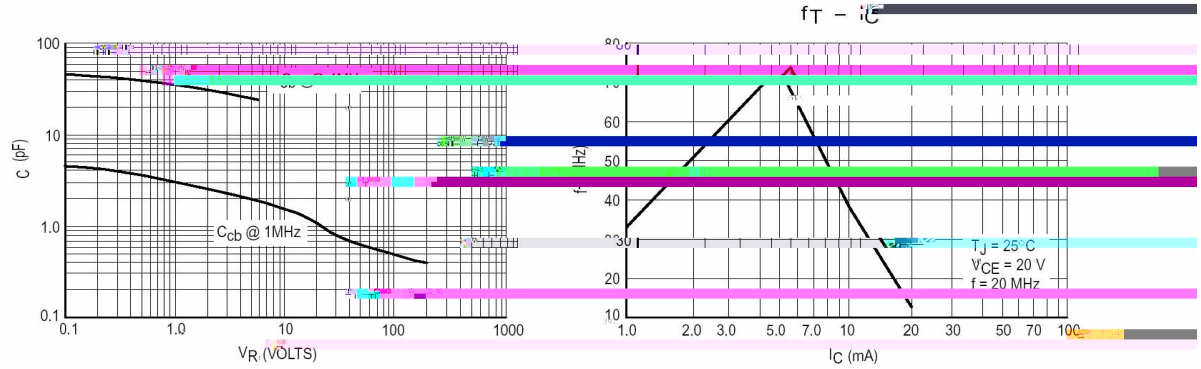
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	200	V
Collector to Emitter Voltage	V_{CEO}	200	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	500	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

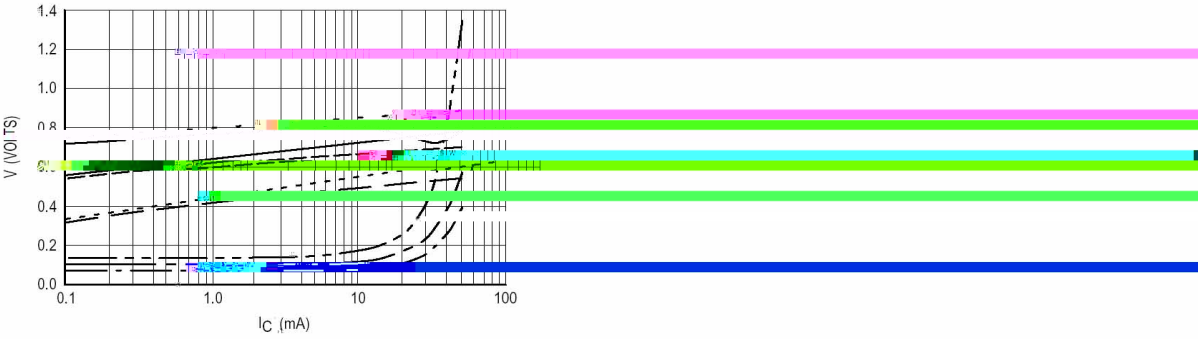
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=100μA I_E=0	200			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA I_B=0	200			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=100μA I_C=0	6.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=160V I_E=0			0.1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=4.0V I_C=0			0.1	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=10V I_C=10mA	40			
	$h_{FE(2)}$	V_{CE}=10V I_C=30mA	40			
	$h_{FE(3)}$	V_{CE}=10V I_C=1.0mA	25			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=20mA I_B=2.0mA			0.5	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=20mA I_B=2.0mA			0.9	V
Transition Frequency	f_T	V_{CE}=20V I_C=10mA f=100MHz	50			MHz
Output Capacitance	C_{ob}	V_{CB}=20V I_E=0 f=1.0MHz			4.0	pF

/ Electrical Characteristic Curve

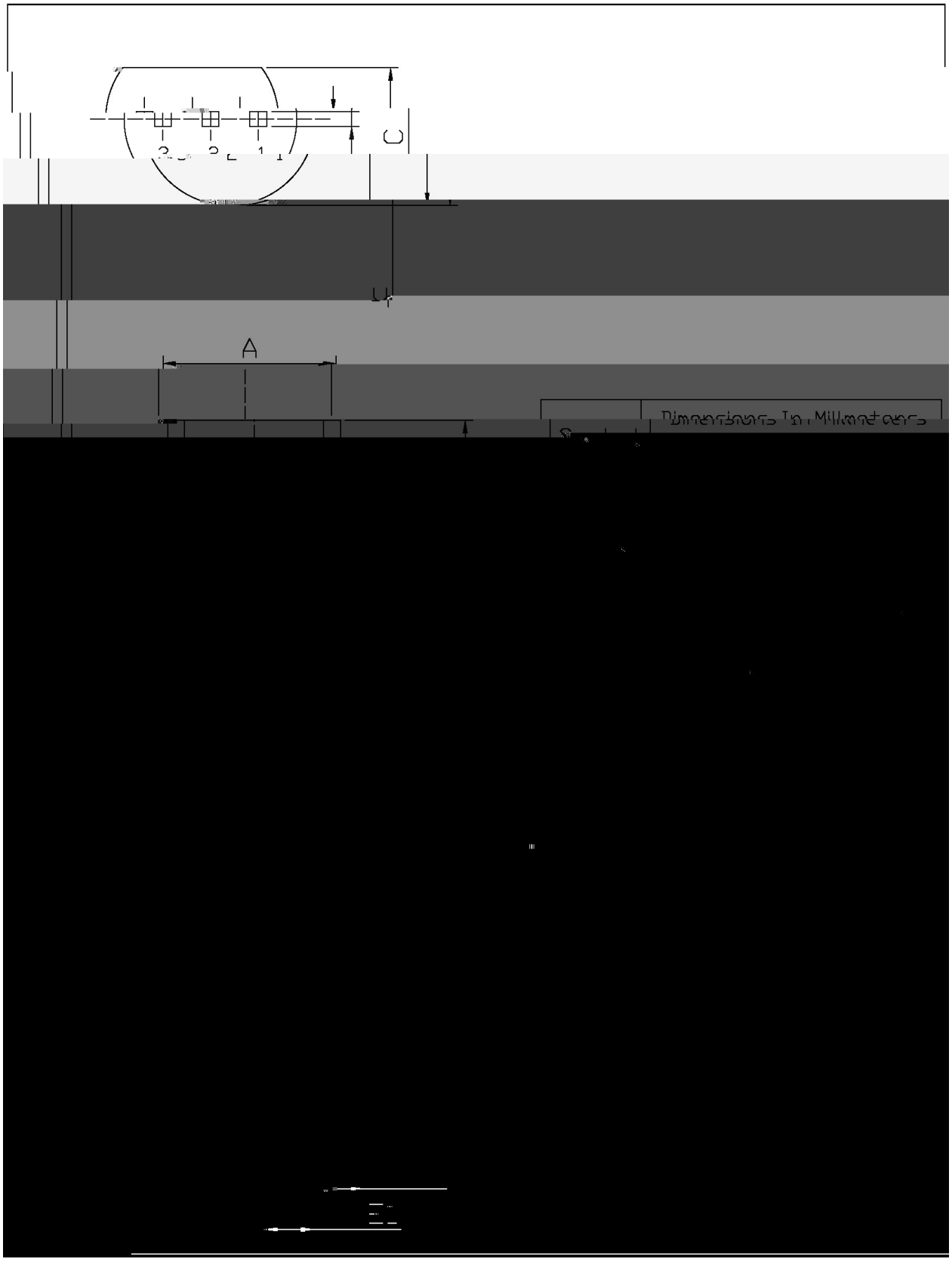




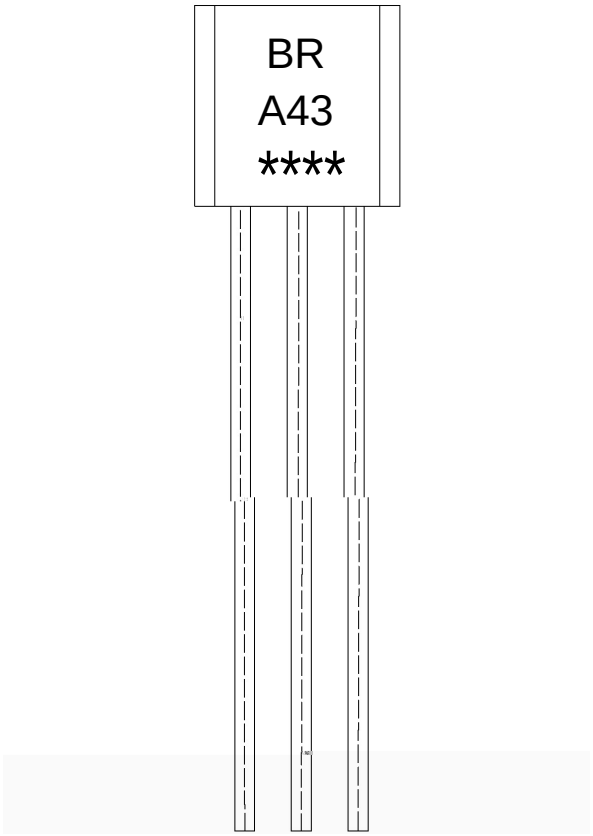


/ Package Dimensions

TO-92 Unit: mm



/ Marking Instructions



Note:

BR:	Company Code.
A43:	Product Type.
****:	Lot No. Code,code change with Lot No.